

TOSHIBA Field Effect Transistor Silicon N-Channel MOS Type (U-MOSVI-H)

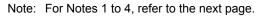
# **TPCA8046-H**

Switching Regulator Applications Motor Drive Applications DC-DC Converter Applications

- Small footprint due to a small and thin package
- High-speed switching
- Small gate charge: Q<sub>SW</sub> = 15 nC (typ.)
- Low drain-source ON-resistance:  $R_{DS}(ON) = 3.5 \text{ m}\Omega$  (typ.)
- High forward transfer admittance:  $|Y_{fs}| = 112 \text{ S}$  (typ.)
- Low leakage current:  $I_{DSS} = 10 \ \mu A (max) (V_{DS} = 40 \ V)$
- Enhancement mode:  $V_{th}$  = 1.3 to 2.3 V (V\_{DS} = 10 V,  $I_{D}$  = 0.5 mA)

#### Absolute Maximum Ratings (Ta = 25°C)

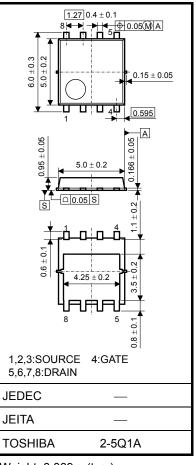
Characte	ristic	Symbol	Rating	Unit
Drain-source voltage		V <sub>DSS</sub>	40	V
Drain-gate voltage (R	t <sub>GS</sub> = 20 kΩ)	V <sub>DGR</sub>	40	V
Gate-source voltage		V <sub>GSS</sub>	±20	V
Drain current	DC (Note 1)	۱ <sub>D</sub>	38	А
	Pulsed (Note 1)	I <sub>DP</sub>	114	A
Drain power dissipati	on (Tc = 25°C)	PD	45	W
Drain power dissipati	on (t = 10 s) (Note 2a)	PD	2.8	W
Drain power dissipati	on (t = 10 s) (Note 2b)	PD	1.6	W
Single-pulse avalance	ne energy (Note 3)	E <sub>AS</sub>	134	mJ
Avalanche current		I <sub>AR</sub>	38	А
Repetitive avalanche (To	energy c = 25°C) (Note 4)	E <sub>AR</sub>	4.34	mJ
Channel temperature		T <sub>ch</sub>	150	°C
Storage temperature	range	T <sub>stg</sub>	–55 to 150	°C



Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the

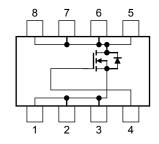
reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

This transistor is an electrostatic-sensitive device. Handle with care.



Weight: 0.069 g (typ.)

#### **Circuit Configuration**



1

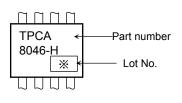
Unit: mm

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### Thermal Characteristics

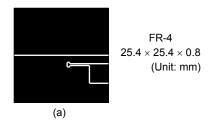
Characteristic	Symbol	Max	Unit
Thermal resistance, channel to case (Tc = 25°C)	R <sub>th (ch-c)</sub>	2.78	°C/W
Thermal resistance, channel to ambient $(t = 10 \text{ s})$ (Note 2a)	R <sub>th (ch-a)</sub>	44.6	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2b)	R <sub>th (ch-a)</sub>	78.1	°C/W

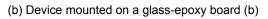
### Marking (Note 5)

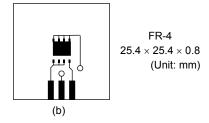


Note 1: Ensure that the channel temperature does not exceed 150  $^\circ\text{C}.$ 

Note 2: (a) Device mounted on a glass-epoxy board (a)







Note 3: V\_DD = 24 V, T\_{ch} = 25 ^{\circ}C (initial), L = 100  $\mu$ H, R\_G = 25  $\Omega$ , I<sub>AR</sub> = 38 A

Note 4: Repetitive rating: pulse width limited by maximum channel temperature

Note 5: \* Weekly code: (Three digits)



Week of manufacture (01 for the first week of the year, continuing up to 52 or 53) Year of manufacture

(The last digit of the year)

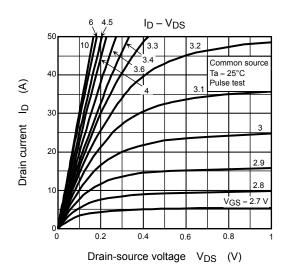
**Electrical Characteristics (Ta = 25°C)** 

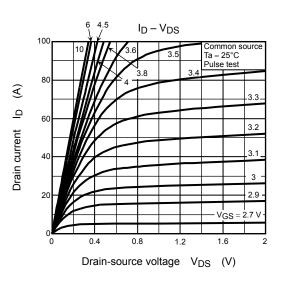
Characteristic		Symbol	Test Condition	Min	Тур.	Max	Unit	
Gate leakage cur	rrent	I <sub>GSS</sub>	$V_{GS}=\pm 20~V,~V_{DS}=0~V$			±100	nA	
Drain cutoff curre	ent	I <sub>DSS</sub>	$V_{DS} = 40 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$			10	μA	
		V (BR) DSS	$V_{(BR) DSS}$ I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	40	_	_	V	
Drain-source bre	n-source breakdown voltage		$I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$	25			v	
Gate threshold ve	oltage	V <sub>th</sub>	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 0.5 \text{ mA}$	1.3	_	2.3	V	
Drain-source ON	ragiotanas	Pro (out)	$V_{GS} = 4.5 \text{ V}, I_D = 19 \text{ A}$	_	4.4	6.3	mΩ	
Drain-source ON	-lesistance	R <sub>DS (ON)</sub>	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 19 \text{ A}$	_	3.5	5.4		
Forward transfer	admittance	Y <sub>fs</sub>	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 19 \text{ A}$	56	112		S	
Input capacitance	9	C <sub>iss</sub>		_	3545	4610	pF	
Reverse transfer	capacitance	C <sub>rss</sub>	$V_{DS} = 10 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ f} = 1 \text{ MHz}$	_	185	270		
Output capacitance		C <sub>oss</sub>		_	600			
Gate resistance		rg	$V_{DS} = 10 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ f} = 1 \text{ MHz}$	_	1.0	1.5	Ω	
Switching time	Rise time	tr	$V_{GS} \stackrel{10}{}_{0}V \prod I_{D} = 19 \text{ A}$	_	4.5	_	• ns	
	Turn-on time	t <sub>on</sub>			14	_		
	Fall time	t <sub>f</sub>			8.9	_		
	Turn-off time	t <sub>off</sub>	$V_{DD}\approx 20 \text{ V}$ Duty $\leq$ 1%, $t_W=10 \ \mu s$	_	48	_		
Total gate charge		0	$V_{DD} \approx 32 \text{ V}, \text{ V}_{GS} = 10 \text{ V}, \text{ I}_{D} = 38 \text{ A}$	_	55	_		
(gate-source plus	s gate-drain)	Qg	$V_{DD}\approx 32~V,~V_{GS}=5~V,~I_{D}=38~A$		29			
Gate-source charge 1		Q <sub>gs1</sub>	$V_{DD} \approx 32$ V, $V_{GS} = 10$ V, $I_D = 38$ A		11		nC	
Gate-drain ("Miller") charge		Q <sub>gd</sub>			8.6			
Gate switch char	ge	Q <sub>SW</sub>	1	_	15	—		

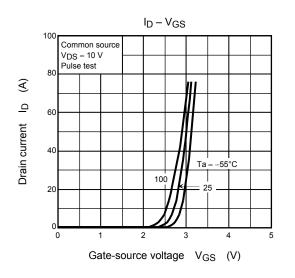
#### Source-Drain Ratings and Characteristics (Ta = 25°C)

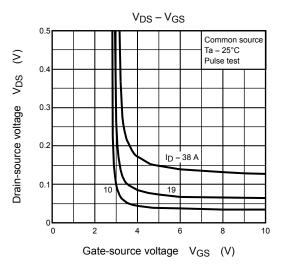
Characteristic		Symbol	Test Condition	Min	Тур.	Max	Unit	
Drain reverse current	Pulse	(Note 1)	I <sub>DRP</sub>	—		_	114	А
Forward voltage (diode)			V <sub>DSF</sub>	$I_{DR} = 38 \text{ A}, V_{GS} = 0 \text{ V}$			-1.2	V

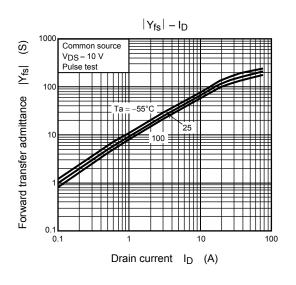
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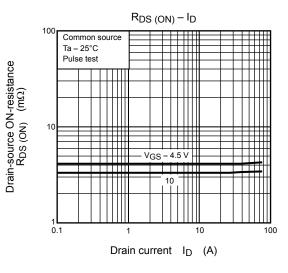




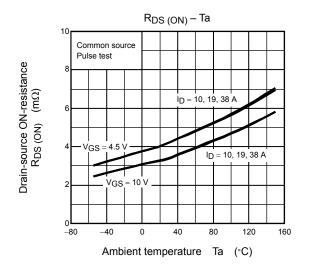


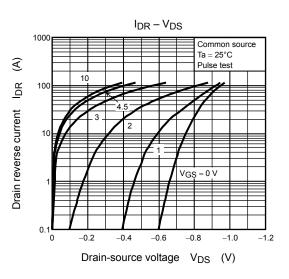


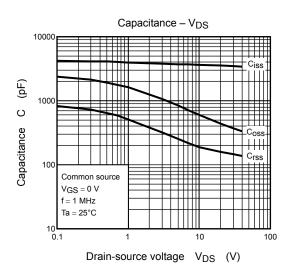


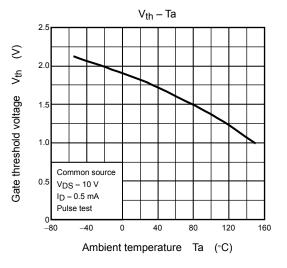


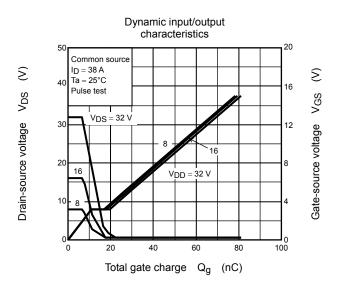
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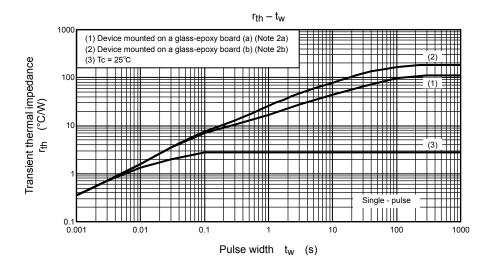


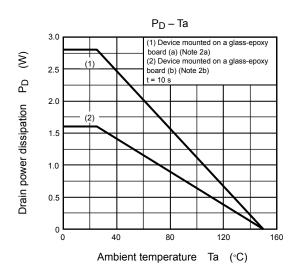


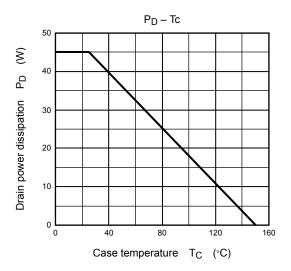


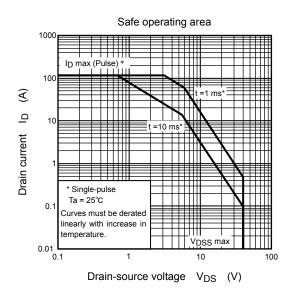












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